

Toru Ujihara

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198
papers

2,885
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41
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215
ext. papers

3,324
ext. citations

2.2
avg, IF

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L-index

#	Paper	IF	Citations
198	In situ observation of elementary growth steps on the surface of protein crystals by laser confocal microscopy. <i>Journal of Crystal Growth</i> , 2004 , 262, 536-542	1.6	89
197	Grain growth behaviors of polycrystalline silicon during melt growth processes. <i>Journal of Crystal Growth</i> , 2004 , 266, 441-448	1.6	89
196	Enhanced quantum efficiency of solar cells with self-assembled Ge dots stacked in multilayer structure. <i>Applied Physics Letters</i> , 2003 , 83, 1258-1260	3.4	86
195	Lipid bilayer membrane with atomic step structure: supported bilayer on a step-and-terrace TiO ₂ (100) surface. <i>Langmuir</i> , 2008 , 24, 11567-76	4	70
194	In situ observations of crystal growth behavior of silicon melt. <i>Journal of Crystal Growth</i> , 2002 , 243, 275-282	1.6	64
193	In-situ observations of melt growth behavior of polycrystalline silicon. <i>Journal of Crystal Growth</i> , 2004 , 262, 124-129	1.6	59
192	Super-High Brightness and High-Spin-Polarization Photocathode. <i>Applied Physics Express</i> , 2008 , 1, 045002.4	2.4	57
191	In situ growth of superconducting NdFeAs(O,F) thin films by molecular beam epitaxy. <i>Applied Physics Letters</i> , 2010 , 97, 042509	3.4	55
190	High-Efficiency Conversion of Threading Screw Dislocations in 4H-SiC by Solution Growth. <i>Applied Physics Express</i> , 2012 , 5, 115501	2.4	54
189	Minority carrier lifetime in polycrystalline silicon solar cells studied by photoassisted Kelvin probe force microscopy. <i>Applied Physics Letters</i> , 2008 , 93, 021902	3.4	53
188	Growth rate and surface morphology of 4H-SiC crystals grown from SiCl ₄ and SiCl ₄ /AlCl ₃ solutions under various temperature gradient conditions. <i>Journal of Crystal Growth</i> , 2014 , 401, 681-685	1.6	50
187	Epitaxial Growth of NdFeAsO Thin Films by Molecular Beam Epitaxy. <i>Applied Physics Express</i> , 2009 , 2, 093002	2.4	50
186	Growth of SiGe bulk crystal with uniform composition by directly controlling the growth temperature at the crystal/melt interface using in situ monitoring system. <i>Journal of Crystal Growth</i> , 2001 , 224, 204-211	1.6	46
185	Kinetic analysis of spinodal decomposition process in FeCr alloys by small angle neutron scattering. <i>Acta Materialia</i> , 2000 , 48, 1629-1637	8.4	46
184	Top-seeded solution growth of three-inch-diameter 4H-SiC using convection control technique. <i>Journal of Crystal Growth</i> , 2014 , 395, 68-73	1.6	45
183	High brightness and high polarization electron source using transmission photocathode with GaAs-GaAsP superlattice layers. <i>Journal of Applied Physics</i> , 2008 , 103, 064905	2.5	45
182	30-kV spin-polarized transmission electron microscope with GaAs/GaAsP strained superlattice photocathode. <i>Applied Physics Letters</i> , 2012 , 101, 033102	3.4	44

181	Solution Growth of SiC Crystal with High Growth Rate Using Accelerated Crucible Rotation Technique. <i>Materials Science Forum</i> , 2006 , 527-529, 119-122	0.4	36
180	Critical current density and grain boundary property of BaFe ₂ (As,P) ₂ thin films. <i>Physica C: Superconductivity and Its Applications</i> , 2013 , 494, 181-184	1.3	35
179	Real Time Magnetic Imaging by Spin-Polarized Low Energy Electron Microscopy with Highly Spin-Polarized and High Brightness Electron Gun. <i>Applied Physics Express</i> , 2010 , 3, 026601	2.4	35
178	Low-dislocation-density 4H-SiC crystal growth utilizing dislocation conversion during solution method. <i>Applied Physics Express</i> , 2014 , 7, 065501	2.4	34
177	Evolution of threading screw dislocation conversion during solution growth of 4H-SiC. <i>APL Materials</i> , 2013 , 1, 022109	5.7	34
176	Effect of aluminum addition on the surface step morphology of 4H-SiC grown from Si-rich solution. <i>Journal of Crystal Growth</i> , 2015 , 423, 45-49	1.6	33
175	Compositional variation in Si-rich SiGe single crystals grown by multi-component zone melting method using Si seed and source crystals. <i>Journal of Crystal Growth</i> , 2002 , 240, 373-381	1.6	32
174	Molecular Beam Epitaxy Growth of Superconducting NdFeAs(O,F) Thin Films Using a F-Getter and a Novel F-Doping Method. <i>Applied Physics Express</i> , 2011 , 4, 083102	2.4	31
173	Thermal emittance measurements for electron beams produced from bulk and superlattice negative electron affinity photocathodes. <i>Journal of Applied Physics</i> , 2007 , 102, 024904	2.5	31
172	Photovoltage Mapping on Polycrystalline Silicon Solar Cells by Kelvin Probe Force Microscopy with Piezoresistive Cantilever. <i>Japanese Journal of Applied Physics</i> , 2007 , 46, 5548-5551	1.4	30
171	Effects of misfit dislocations and AlN buffer layer on the GaInN/GaN phase diagram of the growth mode. <i>Journal of Applied Physics</i> , 2001 , 89, 146-153	2.5	30
170	Nitrogen doping of 4H-SiC by the top-seeded solution growth technique using Si-rich solvent. <i>Journal of Crystal Growth</i> , 2014 , 392, 60-65	1.6	29
169	Coherence of a spin-polarized electron beam emitted from a semiconductor photocathode in a transmission electron microscope. <i>Applied Physics Letters</i> , 2014 , 105, 193101	3.4	29
168	Conversion Mechanism of Threading Screw Dislocation during SiC Solution Growth. <i>Materials Science Forum</i> , 2012 , 717-720, 351-354	0.4	29
167	Influence of Solution Flow on Step Bunching in Solution Growth of SiC Crystals. <i>Crystal Growth and Design</i> , 2013 , 13, 3691-3696	3.5	28
166	Anomalous diffusion in supported lipid bilayers induced by oxide surface nanostructures. <i>Langmuir</i> , 2011 , 27, 9662-5	4	28
165	Ge composition dependence of properties of solar cells based on multicrystalline SiGe with microscopic compositional distribution. <i>Journal of Applied Physics</i> , 2004 , 96, 1238-1241	2.5	28
164	High-speed prediction of computational fluid dynamics simulation in crystal growth. <i>CrystEngComm</i> , 2018 , 20, 6546-6550	3.3	28

163	Growth of SiGe bulk crystals with uniform composition by utilizing feedback control system of the crystal/melt interface position for precise control of the growth temperature. <i>Journal of Crystal Growth</i> , 2003 , 250, 298-304	1.6	27
162	Solution Growth of Self-Standing 6H-SiC Single Crystal Using Metal Solvent. <i>Materials Science Forum</i> , 2004 , 457-460, 123-126	0.4	27
161	Polytype Transformation by Replication of Stacking Faults Formed by Two-Dimensional Nucleation on Spiral Steps during SiC Solution Growth. <i>Crystal Growth and Design</i> , 2012 , 12, 3209-3214	3.5	26
160	The strain effect on the superconducting properties of BaFe ₂ (As, P) ₂ thin films grown by molecular beam epitaxy. <i>Superconductor Science and Technology</i> , 2014 , 27, 065005	3.1	25
159	Solution growth of high-quality 3C-SiC crystals. <i>Journal of Crystal Growth</i> , 2008 , 310, 1438-1442	1.6	25
158	Substrate dependence of the superconducting properties of NdFeAs(O,F) thin films. <i>Solid State Communications</i> , 2012 , 152, 735-739	1.6	24
157	Global simulation of the induction heating TSSG process of SiC for the effects of Marangoni convection, free surface deformation and seed rotation. <i>Journal of Crystal Growth</i> , 2017 , 470, 75-88	1.6	23
156	Crystal quality of a 6H-SiC layer grown over macrodefects by liquid-phase epitaxy: a Raman spectroscopic study. <i>Thin Solid Films</i> , 2005 , 476, 206-209	2.2	23
155	Different behavior of threading edge dislocation conversion during the solution growth of 4H-SiC depending on the Burgers vector. <i>Acta Materialia</i> , 2014 , 81, 284-290	8.4	22
154	Highly spin-polarized electron photocathode based on GaAs/AlAsP superlattice grown on mosaic-structured buffer layer. <i>Journal of Crystal Growth</i> , 2008 , 310, 5039-5043	1.6	22
153	Crystalline Quality Evaluation of 6H-SiC Bulk Crystals Grown from Si-Ti-C Ternary Solution. <i>Materials Science Forum</i> , 2005 , 483-485, 13-16	0.4	21
152	Epitaxial relation and island growth of perylene-3,4,9,10-tetracarboxylic dianhydride (PTCDA) thin film crystals on a hydrogen-terminated Si(1 1 1) substrate. <i>Journal of Crystal Growth</i> , 2004 , 262, 196-201	1.6	20
151	On the origin of strain fluctuation in strained-Si grown on SiGe-on-insulator and SiGe virtual substrates. <i>Applied Physics Letters</i> , 2004 , 85, 1335-1337	3.4	19
150	Effects of high pressure on the growth kinetics of orthorhombic lysozyme crystals. <i>Journal of Crystal Growth</i> , 2003 , 254, 188-195	1.6	19
149	Magnetic Damping of the Temperature-Driven Convection in NaCl Aqueous Solution Using a Static and Homogeneous Field of 10 T. <i>Japanese Journal of Applied Physics</i> , 1999 , 38, L842-L844	1.4	19
148	Polytype-selective growth of SiC by supersaturation control in solution growth. <i>Journal of Crystal Growth</i> , 2012 , 360, 176-180	1.6	18
147	Influence of the elastic strain on the band structure of ellipsoidal SiGe coherently embedded in the Si matrix. <i>Journal of Applied Physics</i> , 2003 , 94, 916-920	2.5	18
146	Enantioselective amplification on circularly polarized laser-induced chiral nucleation from a NaClO ₃ solution containing Ag nanoparticles. <i>CrystEngComm</i> , 2016 , 18, 7441-7448	3.3	18

145	Effects of spacer thickness on quantum efficiency of the solar cells with embedded Ge islands in the intrinsic layer. <i>Applied Physics Letters</i> , 2004 , 84, 2802-2804	3.4	17
144	The Boersch effect in a picosecond pulsed electron beam emitted from a semiconductor photocathode. <i>Applied Physics Letters</i> , 2016 , 109, 013108	3.4	17
143	Non-uniform electrodeposition of zinc on the (0001) plane. <i>Thin Solid Films</i> , 2015 , 590, 207-213	2.2	16
142	Study of minority carrier diffusion length in multicrystalline silicon solar cells using photoassisted Kelvin probe force microscopy. <i>Applied Physics Letters</i> , 2009 , 95, 191908	3.4	16
141	High-quality and large-area 3C β SiC growth on 6H β SiC(0 0 0 1) seed crystal with top-seeded solution method. <i>Journal of Crystal Growth</i> , 2011 , 318, 389-393	1.6	16
140	Physical model for the evaluation of solid-liquid interfacial tension in silicon. <i>Journal of Applied Physics</i> , 2001 , 90, 750-755	2.5	16
139	Numerical investigation of the transport phenomena occurring in the growth of SiC by the induction heating TSSG method. <i>Journal of Crystal Growth</i> , 2017 , 474, 50-54	1.6	15
138	Achiral Metastable Crystals of Sodium Chlorate Forming Prior to Chiral Crystals in Solution Growth. <i>Crystal Growth and Design</i> , 2013 , 13, 5188-5192	3.5	15
137	Reduction of Threading Screw Dislocation Utilizing Defect Conversion during Solution Growth of 4H-SiC. <i>Materials Science Forum</i> , 2013 , 740-742, 189-192	0.4	15
136	Formation process of 3C-SiC on 6H-SiC (0001) by low-temperature solution growth in Si β Cr system. <i>Journal of Crystal Growth</i> , 2011 , 335, 94-99	1.6	15
135	Melt growth of multicrystalline SiGe with large compositional distribution for new solar cell applications. <i>Solar Energy Materials and Solar Cells</i> , 2002 , 72, 93-100	6.4	15
134	Growth and properties of SiGe multicrystals with microscopic compositional distribution for high-efficiency solar cells. <i>Solar Energy Materials and Solar Cells</i> , 2002 , 73, 305-320	6.4	15
133	A simple approach to determine preferential growth orientation using multiple seed crystals with random orientations and its utilization for seed optimization to restrain polycrystallization of SiGe bulk crystal. <i>Journal of Crystal Growth</i> , 2005 , 276, 393-400	1.6	15
132	Conversion Behavior of Threading Screw Dislocations on C Face with Different Surface Morphology During 4H-SiC Solution Growth. <i>Crystal Growth and Design</i> , 2016 , 16, 6436-6439	3.5	14
131	Modification of the surface morphology of 4H-SiC by addition of Sn and Al in solution growth with SiCr solvents. <i>Journal of Crystal Growth</i> , 2017 , 458, 37-43	1.6	14
130	Photovoltage Mapping on Polycrystalline Silicon Solar Cells through Potential Measurements by Atomic Force Microscopy with Piezoresistive Cantilever. <i>Japanese Journal of Applied Physics</i> , 2006 , 45, 2128-2131	1.4	14
129	Two-step SiC solution growth for dislocation reduction. <i>Journal of Crystal Growth</i> , 2017 , 468, 874-878	1.6	13
128	Surface Morphology and Threading Dislocation Conversion Behavior during Solution Growth of 4H-SiC Using Al-Si Solvent. <i>Materials Science Forum</i> , 2014 , 778-780, 67-70	0.4	13

127	New method for measurement of interdiffusion coefficient in high temperature solutions based on Fick's first law. <i>Journal of Crystal Growth</i> , 2002 , 241, 387-394	1.6	13
126	Structural properties of directionally grown polycrystalline SiGe for solar cells. <i>Journal of Crystal Growth</i> , 2005 , 275, 467-473	1.6	13
125	SiGe bulk crystal as a lattice-matched substrate to GaAs for solar cell applications. <i>Applied Physics Letters</i> , 2000 , 77, 3565-3567	3.4	13
124	Emergence and Amplification of Chirality via Achiral-Chiral Polymorphic Transformation in Sodium Chlorate Solution Growth. <i>Crystal Growth and Design</i> , 2014 , 14, 3596-3602	3.5	12
123	Pattern size effect on source supply process for sub-micrometer scale selective area growth by organometallic vapor phase epitaxy. <i>Journal of Crystal Growth</i> , 2006 , 289, 89-95	1.6	12
122	Phase diagram of growth mode for the SiGe/Si heterostructure system with misfit dislocations. <i>Journal of Crystal Growth</i> , 2004 , 260, 372-383	1.6	12
121	In-situ monitoring system of the position and temperature at the crystal/solution interface. <i>Journal of Crystal Growth</i> , 2002 , 236, 125-131	1.6	12
120	Morphology of AlN whiskers grown by reacting N ₂ gas and Al vapor. <i>Journal of Crystal Growth</i> , 2017 , 468, 576-580	1.6	11
119	Plasmonic Heating-Assisted Laser-Induced Crystallization from a NaClO ₃ Unsaturated Mother Solution. <i>Crystal Growth and Design</i> , 2017 , 17, 809-818	3.5	11
118	Dislocation Conversion During SiC Solution Growth for High-Quality Crystals. <i>Materials Science Forum</i> , 2015 , 821-823, 3-8	0.4	11
117	Solubility measurement of a metastable achiral crystal of sodium chlorate in solution growth. <i>Journal of Crystal Growth</i> , 2014 , 394, 106-111	1.6	11
116	Forming two-dimensional structure of DNA-functionalized Au nanoparticles via lipid diffusion in supported lipid bilayers. <i>Journal of Crystal Growth</i> , 2014 , 401, 494-498	1.6	11
115	Effects of defects and local thickness modulation on spin-polarization in photocathodes based on GaAs/GaAsP strained superlattices. <i>Journal of Applied Physics</i> , 2010 , 108, 094509	2.5	11
114	Effect of Li doping on photoluminescence from Er, O-codoped GaAs. <i>Journal of Crystal Growth</i> , 2007 , 298, 69-72	1.6	11
113	Bayesian optimization for a high- and uniform-crystal growth rate in the top-seeded solution growth process of silicon carbide under applied magnetic field and seed rotation. <i>Journal of Crystal Growth</i> , 2020 , 532, 125437	1.6	11
112	Crystal Orientation Dependence of Precipitate Structure of Electrodeposited Li Metal on Cu Current Collectors. <i>Crystal Growth and Design</i> , 2017 , 17, 2379-2385	3.5	10
111	4H-SiC Growth from Si-Cr-C Solution under Al and N Co-Doping Conditions. <i>Materials Science Forum</i> , 2015 , 821-823, 9-13	0.4	10
110	Top-Seeded Solution Growth of 3 Inch Diameter 4H-SiC Bulk Crystal Using Metal Solvents. <i>Materials Science Forum</i> , 2014 , 778-780, 79-82	0.4	10

109	Local concentration of gel phase domains in supported lipid bilayers under light irradiation in binary mixture of phospholipids doped with dyes for photoinduced activation. <i>Langmuir</i> , 2008 , 24, 10974-80	4.80	10
108	Fabrication of SiGe-on-insulator by rapid thermal annealing of Ge on Si-on-insulator substrate. <i>Applied Surface Science</i> , 2004 , 224, 95-98	6.7	10
107	Stacked Ge islands for photovoltaic applications. <i>Science and Technology of Advanced Materials</i> , 2003 , 4, 367-370	7.1	10
106	Assessing composition gradient energy effects due to spin interaction on the spinodal decomposition of FeCr. <i>Materials Science & Engineering A: Structural Materials: Properties, Microstructure and Processing</i> , 2001 , 312, 128-135	5.3	10
105	Numerical investigation of the effect of static magnetic field on the TSSG growth of SiC. <i>Journal of Crystal Growth</i> , 2018 , 498, 140-147	1.6	10
104	Analysis of the carbon transport near the growth interface with respect to the rotational speed of the seed crystal during top-seeded solution growth of SiC. <i>Japanese Journal of Applied Physics</i> , 2016 , 55, 125601	1.4	10
103	Effect of Crystal Orientation of Cu Current Collectors on Cycling Stability of Li Metal Anodes. <i>ACS Applied Materials & Interfaces</i> , 2020 , 12, 9341-9346	9.5	9
102	Septin Interferes with the Temperature-Dependent Domain Formation and Disappearance of Lipid Bilayer Membranes. <i>Langmuir</i> , 2016 , 32, 12823-12832	4	9
101	Increase in the Growth Rate by Rotating the Seed Crystal at High Speed during the Solution Growth of SiC. <i>Materials Science Forum</i> , 2014 , 778-780, 63-66	0.4	9
100	Size uniformity of InAs dots on mesa-structure templates on (001) InP substrates grown by droplet metal-organic vapor phase epitaxy method. <i>Applied Physics Letters</i> , 2006 , 89, 083110	3.4	9
99	Molten metal flux growth and properties of CrSi ₂ . <i>Journal of Alloys and Compounds</i> , 2004 , 383, 319-321	5.7	9
98	Effects of vicinal steps on the island growth and orientation of epitaxially grown perylene-3,4,9,10-tetracarboxylic dianhydride (PTCDA) thin film crystals on a hydrogen-terminated Si(1 1 1) substrate. <i>Journal of Crystal Growth</i> , 2005 , 273, 594-602	1.6	9
97	Growth of SixGe _{1-x} (x fallingdotseq 0.15) Bulk Crystal with Uniform Composition Utilizing in situ Monitoring of the Crystal-solution Interface. <i>Japanese Journal of Applied Physics</i> , 2001 , 40, 4141-4144	1.4	9
96	Phase diagram calculation for epitaxial growth of GaInAs on InP considering the surface, interfacial and strain energies. <i>Journal of Crystal Growth</i> , 2000 , 220, 413-424	1.6	9
95	Effect of magnesium ion concentration on two-dimensional structure of DNA-functionalized nanoparticles on supported lipid bilayer. <i>Japanese Journal of Applied Physics</i> , 2016 , 55, 03DF11	1.4	8
94	Effect of Surface Polarity on the Conversion of Threading Dislocations in Solution Growth. <i>Materials Science Forum</i> , 2013 , 740-742, 15-18	0.4	8
93	Supported lipid bilayer membranes on SiO ₂ and TiO ₂ : substrate effects on membrane formation and shape transformation 2007 ,		8
92	Fabrication of SiGe-on-Insulator through Thermal Diffusion of Ge on Si-on-Insulator Substrate. <i>Japanese Journal of Applied Physics</i> , 2003 , 42, L232-L234	1.4	8

91	Evidence of the Presence of Built-in Strain in Multicrystalline SiGe with Large Compositional Distribution. <i>Japanese Journal of Applied Physics</i> , 2002 , 41, 4462-4465	1.4	8
90	Effect of nonlinearity of the evolution equation on the spinodal decomposition process in alloys. <i>Physical Review B</i> , 1998 , 58, 11371-11376	3.3	8
89	Thin film growth of CaFe ₂ As ₂ by molecular beam epitaxy. <i>Superconductor Science and Technology</i> , 2016 , 29, 015013	3.1	7
88	Molecular beam epitaxy of GaAs on nearly lattice-matched SiGe substrates grown by the multicomponent zone-melting method. <i>Semiconductor Science and Technology</i> , 2001 , 16, 699-703	1.8	7
87	Control of Macroscopic Absorption Coefficient of Multicrystalline SiGe by Microscopic Compositional Distribution. <i>Japanese Journal of Applied Physics</i> , 2002 , 41, L37-L39	1.4	7
86	Geometrical design of a crystal growth system guided by a machine learning algorithm. <i>CrystEngComm</i> , 2021 , 23, 2695-2702	3.3	7
85	Improvement of Surface Morphology by Solution Flow Control in Solution Growth of SiC on Off-Axis Seeds. <i>Materials Science Forum</i> , 2015 , 821-823, 31-34	0.4	6
84	Direct Growth of AlN Single Crystal on Sapphire by Solution Growth Method. <i>Japanese Journal of Applied Physics</i> , 2013 , 52, 08JE17	1.4	6
83	Epitaxial growth of LaFeAs(O,F) thin films by molecular beam epitaxy. <i>Physica C: Superconductivity and Its Applications</i> , 2011 , 471, 1174-1176	1.3	6
82	Effects of absorbed group-V atoms on the size distribution and optical properties of InAsP quantum dots fabricated by the droplet hetero-epitaxy. <i>Journal of Crystal Growth</i> , 2008 , 310, 2239-2243	1.6	6
81	Fabrication of solar cell with stacked Ge islands for enhanced absorption in the infrared regime. <i>Thin Solid Films</i> , 2004 , 451-452, 604-607	2.2	6
80	Effects of growth temperature on the surface morphology of silicon thin films on (111) silicon monocrystalline substrate by liquid phase epitaxy. <i>Journal of Crystal Growth</i> , 2004 , 266, 467-474	1.6	6
79	Simultaneous in situ measurement of solute and temperature distributions in the alloy solutions. <i>Journal of Crystal Growth</i> , 2002 , 242, 313-320	1.6	6
78	High-Quality Crystalline Silicon Layer Grown by Liquid Phase Epitaxy Method at Low Growth Temperature. <i>Japanese Journal of Applied Physics</i> , 2003 , 42, L217-L219	1.4	6
77	Thickness dependence of stable structure of the Stranski-Krastanov mode in the GaPSb/GaP system. <i>Journal of Crystal Growth</i> , 2000 , 209, 637-647	1.6	6
76	In Situ Measurement of Composition in High-Temperature Solutions by X-Ray Fluorescence Spectrometry. <i>Japanese Journal of Applied Physics</i> , 2000 , 39, 5981-5982	1.4	6
75	Intensity Interference in a Coherent Spin-Polarized Electron Beam. <i>Physical Review Letters</i> , 2021 , 126, 125501	7.4	6
74	Application of C-face dislocation conversion to 2 inch SiC crystal growth on an off-axis seed crystal. <i>CrystEngComm</i> , 2019 , 21, 7260-7265	3.3	6

73	Adaptive process control for crystal growth using machine learning for high-speed prediction: application to SiC solution growth. <i>CrystEngComm</i> , 2021 , 23, 1982-1990	3.3	6
72	Change in Surface Morphology by Addition of Impurity Elements in 4H-SiC Solution Growth with Si Solvent. <i>Materials Science Forum</i> , 2015 , 821-823, 14-17	0.4	5
71	Dislocation Behavior in Bulk Crystals Grown by TSSG Method. <i>Materials Science Forum</i> , 2018 , 924, 39-42	0.4	5
70	Development of angle-resolved spectroscopy system of electrons emitted from a surface with negative electron affinity state. <i>Review of Scientific Instruments</i> , 2018 , 89, 073103	1.7	5
69	Direct observation of stacking fault shrinkage in 4H-SiC at high temperatures by in-situ X-ray topography using monochromatic synchrotron radiation. <i>Applied Physics Letters</i> , 2018 , 113, 012101	3.4	5
68	Bulk 3C-SiC Crystal by Top Seeded Solution Growth Method. <i>Materials Science Forum</i> , 2013 , 740-742, 311-314	0.4	5
67	Defect Evaluation of SiC Crystal Grown by Solution Method: The Study by Synchrotron X-Ray Topography and Etching Method. <i>Materials Science Forum</i> , 2011 , 679-680, 28-31	0.4	5
66	Stable Growth of 4H-SiC Single Polytype by Controlling the Surface Morphology Using a Temperature Gradient in Solution Growth. <i>Materials Science Forum</i> , 2012 , 717-720, 53-56	0.4	5
65	Crystal Quality Evaluation of 6H-SiC Layers Grown by Liquid Phase Epitaxy around Micropipes using Micro-Raman Scattering Spectroscopy. <i>Materials Science Forum</i> , 2004 , 457-460, 633-636	0.4	5
64	Growth of InGaAs and SiGe homogeneous bulk crystals which have complete miscibility in the phase diagrams. <i>International Journal of Materials and Product Technology</i> , 2005 , 22, 185	1	5
63	Temperature dependence of double Shockley stacking fault behavior in nitrogen-doped 4H-SiC studied by in-situ synchrotron X-ray topography. <i>Acta Materialia</i> , 2020 , 194, 387-393	8.4	4
62	Phase-locking of oscillating images using laser-induced spin-polarized pulse TEM. <i>Microscopy (Oxford, England)</i> , 2013 , 62, 607-14	1.3	4
61	Solution Growth of SiC Crystals in Si-Ti and Si-Ge-Ti Solvents. <i>Materials Science Forum</i> , 2008 , 600-603, 59-62	0.4	4
60	Fabrication of SiGe bulk crystals with uniform composition as substrates for Si-based heterostructures. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2002 , 89, 364-367	3.1	4
59	Synchrotron X-ray topographic image contrast variation of screw-type basal plane dislocations located at different depths below the crystal surface in 4H-SiC. <i>Acta Materialia</i> , 2021 , 208, 116746	8.4	4
58	The Prediction Model of Crystal Growth Simulation Built by Machine Learning and Its Applications. <i>Vacuum and Surface Science</i> , 2019 , 62, 136-140	0	4
57	In Situ Observation of Chiral Symmetry Breaking in NaClO ₃ Chiral Crystallization Realized by Thermoplasmonic Micro-Stirring. <i>Crystal Growth and Design</i> , 2018 , 18, 4230-4239	3.5	4
56	Adjoint-based sensitivity analysis for the optimal crucible temperature profile in the RF-Heating TSSG-SiC crystal growth process. <i>Journal of Crystal Growth</i> , 2019 , 517, 59-63	1.6	3

55	Control of Interface Shape by Non-Axisymmetric Solution Convection in Top-Seeded Solution Growth of SiC Crystal. <i>Materials Science Forum</i> , 2015 , 821-823, 18-21	0.4	3
54	Effect of Forced Convection by Crucible Design in Solution Growth of SiC Single Crystal. <i>Materials Science Forum</i> , 2015 , 821-823, 22-25	0.4	3
53	Research on Solvent Composition for Different Surface Morphology on C Face during 4H-SiC Solution Growth. <i>Materials Science Forum</i> , 2015 , 821-823, 39-42	0.4	3
52	Characterization of V-Shaped Defects Formed during the 4H-SiC Solution Growth by Transmission Electron Microscopy and X-ray Topography Analysis. <i>Crystal Growth and Design</i> , 2016 , 16, 5136-5140	3.5	3
51	Temperature dependence of carrier relaxation time in gallium phosphide evaluated by photoemission measurements. <i>AIP Advances</i> , 2017 , 7, 115314	1.5	3
50	Growth of a smooth CaF ₂ layer on NdFeAsO thin film. <i>Journal of Physics: Conference Series</i> , 2014 , 507, 012047	0.3	3
49	Analysis of thickness modulation in GaAs/GaAsP strained superlattice by TEM observation. <i>Journal of Crystal Growth</i> , 2012 , 353, 84-87	1.6	3
48	Polytype Stability of 4H-SiC Seed Crystal on Solution Growth. <i>Materials Science Forum</i> , 2011 , 679-680, 24-27	0.4	3
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